

AMENDMENTS TO THE SPECIFICATION:

Please replace the disclosure beginning at line 7 of page 1 and spanning to line 12 of page 1 with the following rewritten disclosure:

Cross-Reference To Related Patents

This application is a divisional of application Serial No. 09/738,760, filed February 14, 2001, now issued as U.S. Letters Patent No. 6,632,732 entitled "Structure and Method of Making a Sub-Micron MOS Transistor," invented by Ma *et al.*, which is a continuation-in-part of application Serial No. 09/004,991, filed January 9, 1998, now issued as U.S. Letters Patent No. 6,274,421 entitled "Method of Making Metal Gate Sub-Micron MOS Transistor," invented by Hsu *et al.*

Please replace the disclosure beginning at line 2 of page 2 and spanning to line 9 of page 2 with the following rewritten disclosure:

A method of fabricating a sub-micron MOS transistor includes preparing a substrate, including isolating an active region therein, depositing a gate oxide layer; depositing a first selective etchable layer over the gate oxide layer, depositing a second selective etchable layer over the first selective etchable layer; etching the structure to undercut the first selective etchable layer; implanting ions in the active region to form a source region and a drain region; depositing and planarizing the oxide; removing the remaining first selective etchable layer and the second selective etchable

layer; depositing a gate electrode; and depositing oxide and metalizing the structure.

Please replace the disclosure beginning at line 10 of page 3 and spanning to line 14 of page 3 with the following rewritten disclosure:

Turning to Fig. 2, a gate oxide layer 18 is formed, and a layer of silicon nitride (Si_3N_4), or polysilicon, 20, also referred to herein as a first selectable etchable layer, is deposited to a thickness of between about 200 nm to 500 nm. A thin layer of oxide 22, also referred to herein as a second selective etchable layer, is deposited over the nitride layer to a thickness of between about 20 nm to 100 nm.